

SBD10150CT、SBDF10150CT

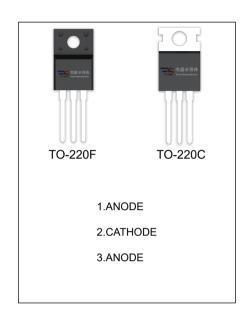
SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

Io	10 (2×5) A
V_{RRM}	150 V
T _j	150 ℃
$V_{F(typ)}$	0.69V (@Tj=125℃)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Cymphol	Parameter	SBD		l loit	
Symbol	Parameter		F10150CT	Unit	
V _{RRM}	Peak repetitive reverse voltage	150			
V_{RWM}	Working peak reverse voltage			V	
V_R	DC blocking voltage				
V _{R(RMS)}	RMS reverse voltage	105		٧	
Io	Average rectified output current	10		Α	
I _{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	120		Α	
R _{⊙Jc}	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W	
R _{OJA}	Thermal resistance from junction to ambient	62.5		°C/W	
T _j	Junction temperature	150		$^{\circ}$	
T _{stg}	Storage temperature	-55~+150		$^{\circ}$	

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Min Typ 150	Max	Unit V
Reverse voltage	V _(BR)			150			
Reverse current	I _R	V _R =150V	Tj =25℃		2.0	100	uA
			Tj =125℃		2.0		mA
Forward voltage	V _F	I _F =3A	Tj =25℃		0.78		V
			Tj =125℃		0.64		V
		I _F =5A	Tj =25℃		0.80	0.87	V
			Tj =125℃		0.69		V

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



